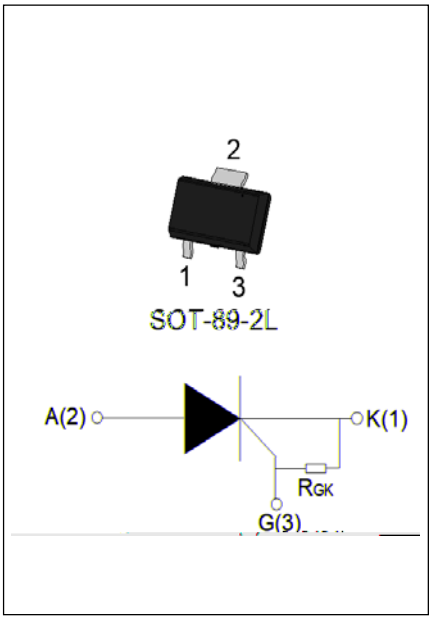
JR0205N2 2A SCR Rev.A.1.1

DESCRIPTION:

The JR0205N2 SCR with the parallel resistor between Gate and Cathode, R_{GK} a N È is especially recommended for use on straight hair, igniter, anion generator, etc. Package SOT-89-2L is RoHS compliant.



MAIN FEATURES

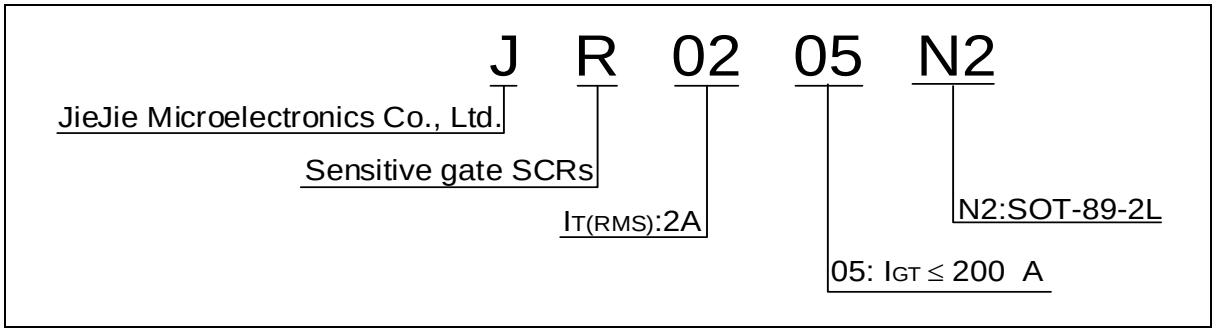
Symbol	Value	Unit
$I_{T(RMS)}$	2	A
V_{DRM}/V_{RRM}	600	V
I_{GT}	”	A

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125 [7]	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	600	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	600	V
Average on-state current (T_C 058)	$I_{T(AV)}$	1.3	A
RMS on-state current (T_C 058)	$I_{T(RMS)}$	2	A
Non repetitive surge peak on-state current (t_p=10ms , T_j=25)	I_{TSM}	20	A
Non repetitive surge peak on-state current (t_p=8.3ms , T_j=25)		22	
I^2t value for fusing (t_p=10ms , T_j=25)	I^2t	2	A^2s
Critical rate of rise of on-state current (I_G=2× I_{GT} , f=100Hz , T_j=125)	dI/dt	50	A s
Peak gate current (t_p=20 s, T_j=125)	I_{GM}	1.2	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.2	W

Peak gate power	P_{GM}	2	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	0.5	kV

ORDERING INFORMATION



MARKING

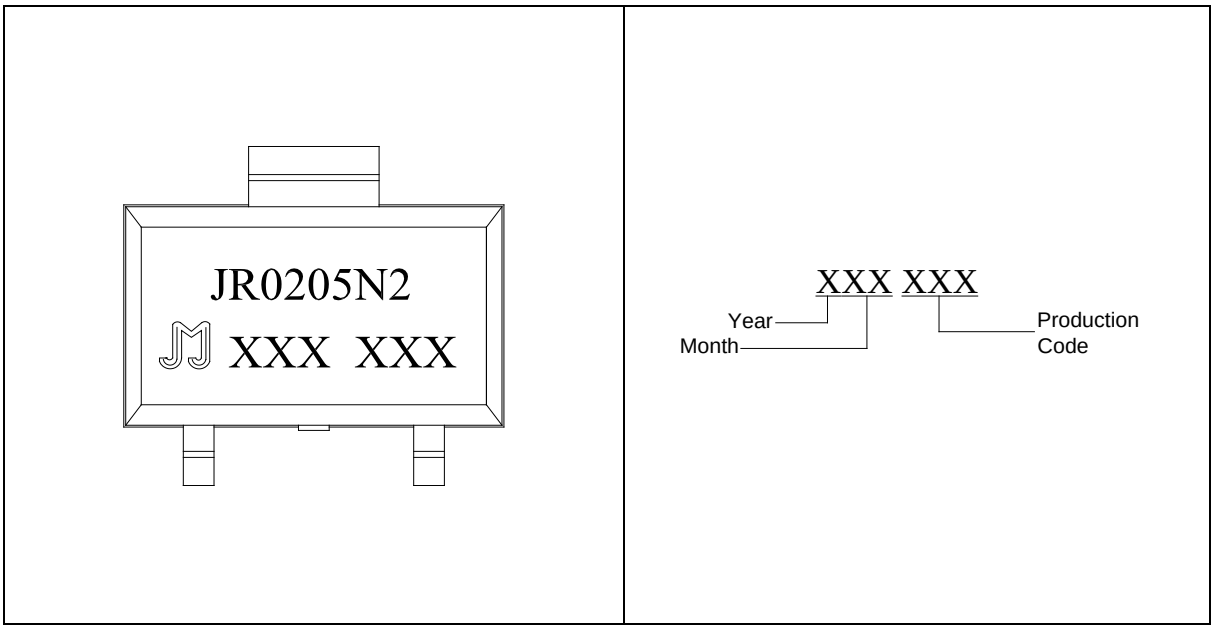


FIG.1: Maximum power dissipation versus RMS on-state current

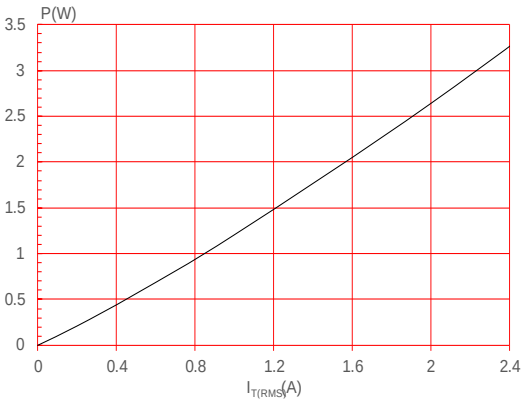


FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

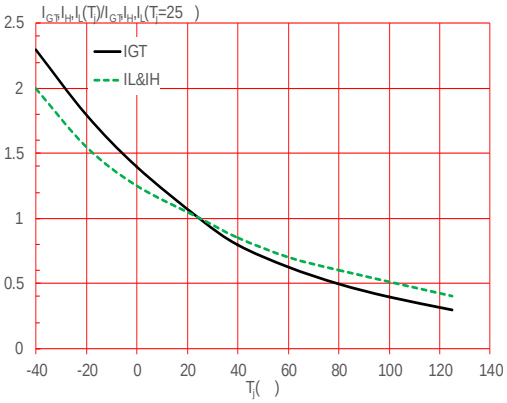
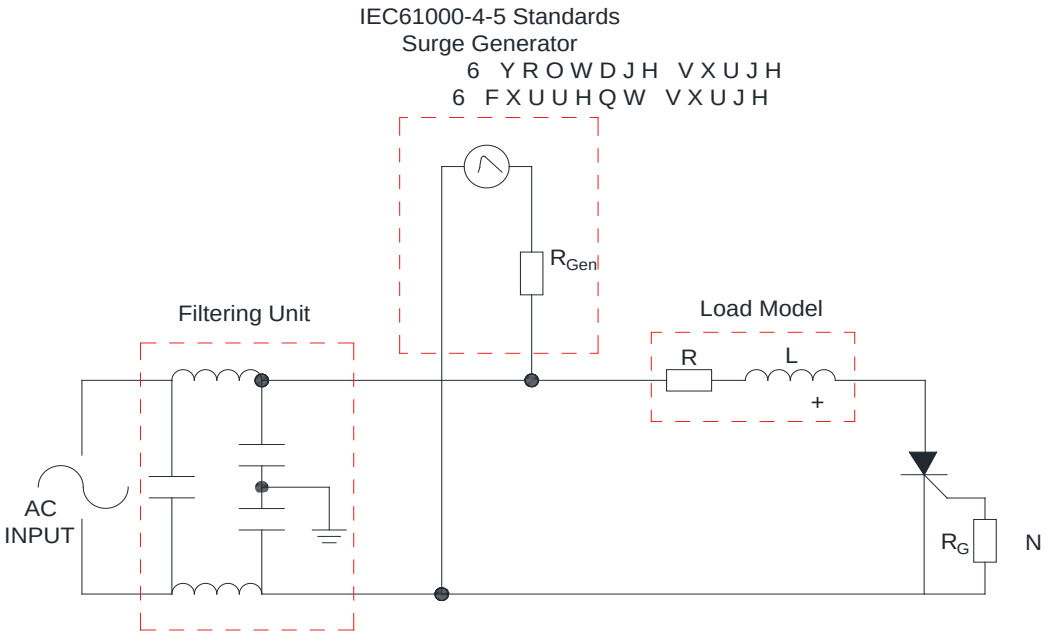


FIG.8 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



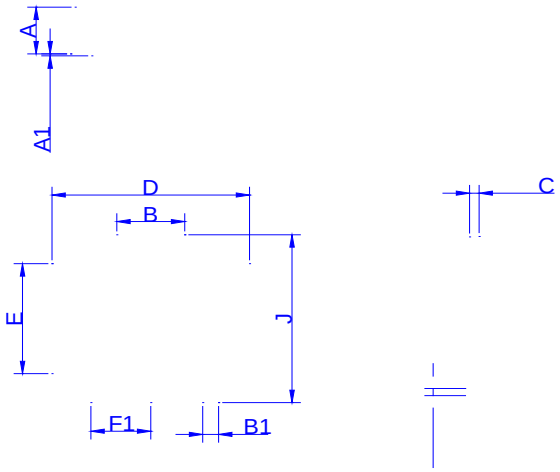
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT)	Package	Base qty. (pcs)	Delivery mode
JR0205N2	600	200	SOT-89-2L	4,000	Tape & Reel

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



DELIVERY MODE

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
P2	1.90	2.00	2.10	0.075	0.079	0.082
D	-	1.50	1.60	-	0.059	0.063
D1	1.50			0.059		
P0	3.90	4.00	4.10	0.154	0.157	0.161
10P0	39.80	40.00	40.20	1.567	1.575	1.583
W			12.30			0.482
P	7.90	8.00	8.10	0.311	0.315	0.319
A0	5.20	5.30	5.40	0.204	0.208	0.212
B0	4.80	4.90	5.00	0.188	0.192	0.196
K0	1.75	1.85	1.95			
t	0.20	0.25	0.30			
	3°		5°			

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